

SEMICONDUCTOR PACKAGE, METHOD OF MANUFACTURING THE SAME, AND SEMICONDUCTOR DEVICE

Abstract

A wiring layer for serving as a first electrode layer of a capacitor portion patterned in a predetermined shape on an insulative base member is formed. A resin layer for serving as a dielectric layer of the capacitor portion is formed on a surface of the wiring layer using an electrophoretic process. Another wiring layer for serving as a second electrode layer of the capacitor portion patterned in a predetermined shape by patterning on the insulative base member inclusive of the resin layer is formed.